

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Cancelled)

2. (Currently Amended) A nonvolatile variable resistor comprising:
a first electrode and a second electrode facing each other and formed on a substrate;
a nonvolatile variable resistance body formed between the first electrode and the second
electrode, wherein the first electrode and the second electrode face each other in a
direction of a surface of the substrate~~A nonvolatile variable resistor according to claim 1,~~
wherein the nonvolatile variable resistance body is formed on an outer surface of the first electrode, and the second electrode is formed on an outer surface of the nonvolatile variable resistance body.

3. (Original) A nonvolatile variable resistor according to claim 2, wherein the first electrode is columnar or prismatic.

4. (Original) A nonvolatile variable resistor according to claim 3, wherein the nonvolatile variable resistance body is made of a manganese oxide of a perovskite structure.

5. (Currently Amended) A nonvolatile variable resistor according to claim 4,
| wherein | the manganese oxide is any of Pr_(1-x)Ca_xMnO₃, La_(1-x)Ca_xMnO₃, and La_(1-x-y)Ca_xPb_yMnO₃~~Pr_{sub.(1-x)}Ca_{sub.x}MnO_{sub.3}~~, ~~La_{sub.(1-x)}Ca_{sub.x}MnO_{sub.3}~~ and ~~La_{sub.(1-x-y)}Ca_{sub.x}Pb_{sub.y}MnO_{sub.3}~~.

6. (Currently Amended) A nonvolatile variable resistor according to claim 5, wherein the manganese oxide is any of Pr_{0.7}Ca_{0.3}MnO₃, La_{0.65}Ca_{0.35}MnO₃ and La_{0.65}Ca_{0.175}Pb_{0.175}MnO₃Pr._{sub.0.7}Ca._{sub.0.3}MnO._{sub.3}, La._{sub.0.65}Ca._{sub.0.35}MnO._{sub.3} and La._{sub.0.65}Ca._{sub.0.175}Pb._{sub.0.175}MnO._{sub.3}.

7. (Cancelled)

8. (Cancelled)

9. (Currently Amended) A nonvolatile variable resistor comprising:
a first electrode and a second electrode facing each other and formed on a substrate;
a nonvolatile variable resistance body formed between the first electrode and the second
electrode, the first electrode and the second electrode face each other in a direction of a
surface of the substrate, the first electrode being columnar or prismatic A nonvolatile
variable resistor according to claim 8, ; wherein the nonvolatile variable resistance body
is made of a manganese oxide of a perovskite structure, and wherein the manganese
oxide is any of Pr_(1-x)Ca_xMnO₃, La_(1-x)Ca_xMnO₃, and La_(1-x-y)Ca_xPb_yMnO₃Pr._{sub.(1-}
x)Ca._{sub.x}MnO._{sub.3}, La._{sub.(1-x)}Ca._{sub.x}MnO._{sub.3} and La._{sub.(1-x-}
y)Ca._{sub.x}Pb._{sub.y}MnO._{sub.3}.

10. (Currently Amended) A nonvolatile variable resistor according to claim 9, wherein the manganese oxide is any of Pr_{0.7}Ca_{0.3}MnO₃, La_{0.65}Ca_{0.35}MnO₃ and La_{0.65}Ca_{0.175}Pb_{0.175}MnO₃Pr._{sub.0.7}Ca._{sub.0.3}MnO._{sub.3}, La._{sub.0.65}Ca._{sub.0.35}MnO._{sub.3} and La._{sub.0.65}Ca._{sub.0.175}Pb._{sub.0.175}MnO._{sub.3}.

11. (Currently Amended) A nonvolatile variable resistor according to claim 427, wherein the nonvolatile variable resistance body is made of a manganese oxide of a perovskite structure.

12. (Currently Amended) A nonvolatile variable resistor according to claim 11, wherein the manganese oxide is any of Pr_(1-x)Ca_xMnO₃, La_(1-x)Ca_xMnO₃, and La_(1-x-y)Ca_xPb_yMnO₃ ~~Pr_(1-x)Ca_xMnO₃~~, ~~La_(1-x)Ca_xMnO₃~~ and ~~La_(1-x-y)Ca_xPb_yMnO₃~~.

13. (Currently Amended) A nonvolatile variable resistor according to claim 12, wherein the manganese oxide is any of Pr_{0.7}Ca_{0.3}MnO₃, La_{0.65}Ca_{0.35}MnO₃ and La_{0.65}Ca_{0.175}Pb_{0.175}MnO₃ ~~Pr_{0.7}Ca_{0.3}MnO₃~~, ~~La_{0.65}Ca_{0.35}MnO₃~~, ~~La_{0.65}Ca_{0.175}Pb_{0.175}MnO₃~~, ~~La_{0.65}Ca_{0.35}MnO₃~~ and ~~La_{0.65}Ca_{0.175}Pb_{0.175}MnO₃~~.

14. (Withdrawn) A memory device having arrangement of memory cells in a matrix on a substrate, each memory cell being constituted of a nonvolatile variable resistor and a selective device, connected to the nonvolatile variable resistor, for selecting the nonvolatile variable resistor, characterized in that

the nonvolatile variable resistor comprises: a first electrode and a second electrode facing each other in a direction of a surface of the substrate and formed on the substrate; and a nonvolatile variable resistance body formed between the first electrode and the second electrode.

15. (Withdrawn) A memory device according to claim 14, wherein the nonvolatile variable resistance body is formed on an outer surface of the first electrode, and the second electrode is formed on an outer surface of the nonvolatile variable resistance body.

16. (Withdrawn) A memory device according to claim 15, wherein the first electrode is columnar or prismatic.

17. (Withdrawn) A memory device according to claim 16, wherein the nonvolatile variable resistance body is made of a manganese oxide of a perovskite structure.

18. (Withdrawn) A memory device according to claim 17, wherein the manganese oxide is any of $\text{Pr}_{\text{sub.}}(1-\text{x})\text{Ca}_{\text{sub.}}\text{xMnO}_{\text{sub.}}3$, $\text{La}_{\text{sub.}}(1-\text{x})\text{Ca}_{\text{sub.}}\text{xMnO}_{\text{sub.}}3$ and $\text{La}_{\text{sub.}}(1-\text{x}-\text{y})\text{Ca}_{\text{sub.}}\text{xPb}_{\text{sub.}}\text{yMnO}_{\text{sub.}}3$.

19. (Withdrawn) A memory device according to claim 14, wherein the selective device selects one from the nonvolatile variable resistors to control a current applied to the one of the nonvolatile variable resistors.

20. (Withdrawn) A memory device according to claim 19, wherein the selective device is a transistor or a diode formed on the substrate.

21. (Withdrawn) A memory device according to claim 20, wherein the transistor is a MOS transistor, and a drain of the MOS transistor is connected to the first electrode.

22. (Withdrawn) A memory device according to claim 20, wherein a cathode of the diode is connected to the first electrode.

23. (Withdrawn) A memory device according to claim 19, wherein the memory cells each have a word line connected to the selective device and a bit line connected to the nonvolatile variable resistor, and the second electrode is connected to the bit line.

24. (Withdrawn) A memory device according to claim 14, wherein the memory cells each have a word line connected to the selective device and a bit line connected to the nonvolatile variable resistor, and the second electrode is connected to the bit line.

25. (Withdrawn) A scaling method of a nonvolatile variable resistor including a first electrode and a second electrode facing each other in a direction of a surface of a substrate and formed thereon, and a nonvolatile variable resistance body formed between the first electrode and the second electrode, the method comprising the steps of:
applying reduction scaling to a planar dimension of the first electrode; and
applying magnification scaling to a height dimension of the first electrode.

26. (Withdrawn) A scaling method of a nonvolatile variable resistor according to claim 25, wherein

the reduction scaling is applied at a magnification of $1/k$ times ($k > 1$), while the magnification scaling is applied at a magnification of k times.

27. (New) A nonvolatile variable resistor comprising:
a first electrode and a second electrode facing each other and formed on a substrate;
a semiconductor switching element formed in the substrate, the switching element being connected to the first electrode;
a nonvolatile variable resistance body formed between the first electrode and the second electrode, a composition of the nonvolatile variable resistance body being chosen to facilitate nonvolatility of the variable resistor;
wherein the first electrode and the second electrode face each other in a direction of a surface of the substrate, wherein the nonvolatile variable resistance body is formed

on an outer surface of the first electrode, and wherein the second electrode is formed on an outer surface of the nonvolatile variable resistance body.

28. (New) A nonvolatile variable resistor according to claim 27, wherein the nonvolatile variable resistance body is formed on an outer surface of the first electrode, and the second electrode is formed on an outer surface of the nonvolatile variable resistance body.

29. (New) A nonvolatile variable resistor according to claim 28, wherein the first electrode is columnar or prismatic.

30. (New) A nonvolatile variable resistor comprising: a first electrode and a second electrode facing each other and formed on a substrate; and a nonvolatile variable resistance body formed between the first electrode and the second electrode, characterized in that

the first electrode and the second electrode face each other in a direction of a surface of the substrate; and

wherein the first electrode is columnar or prismatic.

31. (New) A nonvolatile variable resistor according to claim 30, wherein the nonvolatile variable resistance body is made of a manganese oxide of a perovskite structure.

32. (New) A nonvolatile variable resistor according to claim 35, wherein the manganese oxide is any of $\text{Pr}_{(1-x)}\text{Ca}_x\text{MnO}_3$, $\text{La}_{(1-x)}\text{Ca}_x\text{MnO}_3$, and $\text{La}_{(1-x-y)}\text{Ca}_x\text{Pb}_y\text{MnO}_3$.

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33. (New) A nonvolatile variable resistor according to claim 36, wherein the manganese oxide is any of $\text{Pr}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$, $\text{La}_{0.65}\text{Ca}_{0.35}\text{MnO}_3$ and $\text{La}_{0.65}\text{Ca}_{0.175}\text{Pb}_{0.175}\text{MnO}_3$.